Notice of Allowability	Application No.	Applicant(s)	Applicant(s) KIM, KWANG-TAE	
	10/613,412	KIM KWANG-TAF		
	Examiner	Art Unit		
en norden med de d	Tu-Tu Ho	2818	And	
The MAILING DATE of this communication app All claims being allowable, PROSECUTION ON THE MERITS IS herewith (or previously mailed), a Notice of Allowance (PTOL-85 NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT R of the Office or upon petition by the applicant. See 37 CFR 1.31	6 (OR REMAINS) CLOSED i) or other appropriate comm RIGHTS. This application is:	ith the correspondence addre	ed	
1. A This communication is responsive to Papers filed 07/03/20				
2. ☑ The allowed claim(s) is/are <u>1-14</u> .				
3. ☑ The drawings filed on <u>03 July 2003</u> are accepted by the E	xaminer		***	
 4. Acknowledgment is made of a claim for foreign priority unally a) All b) Some* c) None of the: 1. Certified copies of the priority documents have 2. Certified copies of the priority documents have 	nder 35 U.S.C. § 119(a)-(d)			
Copies of the certified copies of the priority do	cuments have been received	d in this national stage continut	: f 41	
International Bureau (PCT Rule 17.2(a)).	odinerits have been received	u in triis national stage applicat	ion from the	
* Certified copies not received:	. • • • • • • • • • • • • • • • • • • •			
Applicant has THREE MONTHS FROM THE "MAILING DATE" noted below. Failure to timely comply will result in ABANDONM THIS THREE-MONTH PERIOD IS NOT EXTENDABLE.	IENT of this application.			
5. A SUBSTITUTE OATH OR DECLARATION must be subm INFORMAL PATENT APPLICATION (PTO-152) which give	es reason(s) why the oath or	AMINER'S AMENDMENT or NO declaration is deficient.	OTICE OF	
6. CORRECTED DRAWINGS (as "replacement sheets") mus	st be submitted.			
(a) Including changes required by the Notice of Draftspers	on's Patent Drawing Review	v (PTO-948) attached		
1) hereto or 2) to Paper No./Mail Date		V14		
(b) ☐ including changes required by the attached Examiner's Paper No./Mail Date	s Amendment / Comment or	in the Office action of		
ldentifying indicia such as the application number (see 37 CFR 1. each sheet. Replacement sheet(s) should be labeled as such in the	84(c)) should be written on the	e drawings in the front (not the b	pack) of	
7. DEPOSIT OF and/or INFORMATION about the deposit attached Examiner's comment regarding REQUIREMENT I	sit of BIOLOGICAL MATE	RIAL must be submitted N	ote the	
		:		
A44			•	
Attachm nt(s) . ☑ Notice of References Cited (PTO-892)	5 Notice of Inf	ormal Patent Application (PTO-		
Notice of Draftperson's Patent Drawing Review (PTO-948)		ormai Faterit Application (PTO- immary (PTO-413),	152)	
☐ Information Disclosure Statements (PTO-1449 or PTO/SB/08 Paper No./Mail Date	Paper No./N	Mail Date Amendment/Comment		
Examiner's Comment Regarding Requirement for Deposit	8. 🛛 Examiner's S	Statement of Reasons for Allow	/ance	
of Biological Material	9. 🗌 Other			
<u> </u>	11.			
Supervise	Jayfd Nelms ory Patent Examiner Plogy Center 2800			

Application/Control Number: 10/613,412

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DETAILED ACTION

Priority

1. Receipt is acknowledged of papers submitted under 35 U.S.C. 119(a)-(d), which papers have been placed of record in the file.

Allowable Subject Matter

2. Claims 1-14 are allowable over the prior art of record.

The following is an examiner's statement of reasons for allowance: The prior art of record fails to teach or render obvious a memory device and a method of fabricating thereof having all exclusive limitations as recited in claims 1, 5, and 10, comprising a first transistor, a second transistor, a substrate including active regions, a first conductive layer pattern, an insulating layer, a second conductive layer pattern, a first conductive line, and a second conductive line, wherein each of the first transistor and the second transistor comprises the first conductive layer pattern and the second conductive layer pattern, characterized in that either the first conductive layer pattern of the first transistor is floated (referred to as a floating gate stack in the art) or the first transistor further includes a tunnel insulating layer (referred to as a floating gate stack in the art), that the second conductive layer pattern of the first transistor is connected from a memory cell to an adjacent memory cell and constitutes the first conductive line (referred to as a sense line or word line in the art), that the first conductive layer pattern and the second conductive plugs, and

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that either the second transistor constitutes a select transistor or the second conductive pattern of the second transistor is connected to the second conductive line which is also termed a word line.

Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance."

Conclusion

- 3. The prior art made of record and not relied upon is considered pertinent to applicant's disclosure. Copies of the references are not being furnished with this Office Action per MPEP § 707.05(a).
- a) U.S. Patent 6,316,317 to Kawata et al. discloses a 2-T memory cell where thickness of a first gate insulating layer of the selection transistor is smaller than the thickness of a second gate insulating layer of the memory transistor.
- b) U.S. Patent 6,555,869 to Park discloses a 2-T memory cell where each of the source and drain of each of the transistor has a first doped region and a second doped region.
- 4. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Tu-Tu Ho whose telephone number is (571) 272-1778. The examiner can normally be reached on 6:30 am 5:00 pm.

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If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, DAVID NELMS can be reached on (571) 272-1787. The fax phone numbers for the organization where this application or proceeding is assigned are (703) 872-9306 for regular communications and (703) 872-9306 for After Final communications.

Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the receptionist whose telephone number is (703) 308-1782.

TH

Tu-Tu Ho May 20, 2004 David Nelms Supervisory Patent Examiner Technology Center 2800